

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1-2. (Canceled)

3. (Currently Amended) ~~The semiconductor laser device as defined by claim 1~~

A semiconductor laser element that exhibits self-sustained pulsation in a predetermined output region, said semiconductor laser element comprising:

a substrate;

a first conductive type clad layer formed on said substrate;

an active layer formed on said first conductive type clad layer for emitting light by current injection;

a second conductive type first clad layer formed on said active layer; and

a stripe-shaped second conductive type second clad layer formed on said second conductive type first clad layer in a first direction, in such a manner that the cross-sectional surface of said stripe-shaped second conductive type second clad layer in a direction perpendicular to said first direction has a shape having an upper edge and a lower edge that face each other and side edges that connect between said upper edge and said lower edge, where the minimum width thereof is at least 70% but no more than 100% of the maximum width,

wherein the angle between each of said side edges and said lower edge of said stripe-shaped second conductive type second clad layer is at least 70° but no more than 100° at a portion that is at least 60% of the upper side of said stripe-shaped second conductive type second clad layer, and

wherein the shape of said cross-sectional surface of said stripe-shaped second conductive type second clad layer is any one of the following:

a shape such that the width of said upper edge is greater than the width of said lower edge, and each of said side edges narrows inward from said upper edge to said lower edge; and

a shape such that the width of said upper edge is greater than the width of said lower edge, and each of said side edges has an upper side edge portion that descends in a manner that narrows inward from said upper edge towards said lower edge and a lower side edge portion that extends from that upper edge portion to said lower edge.

4. (Currently Amended) ~~The semiconductor laser device as defined by claim 1~~

A semiconductor laser element that exhibits self-sustained pulsation in a predetermined output region, said semiconductor laser element comprising:

a substrate;

a first conductive type clad layer formed on said substrate;

an active layer formed on said first conductive type clad layer for emitting light by current injection;

a second conductive type first clad layer formed on said active layer; and

a stripe-shaped second conductive type second clad layer formed on said second conductive type first clad layer in a first direction, in such a manner that the cross-sectional surface of said stripe-shaped second conductive type second clad layer in a direction perpendicular to said first direction has a shape having an upper edge and a lower edge that face each other and side edges that connect between said upper edge and said lower edge, where the minimum width thereof is at least 70% but no more than 100% of the maximum width,

wherein the angle between each of said side edges and said lower edge of said stripe-shaped second conductive type second clad layer is at least 70° but no more

than 100° at a portion that is at least 60% of the upper side of said stripe-shaped second conductive type second clad layer, and

wherein said cross-sectional surface of said stripe-shaped second conductive type second clad layer has a shape such that the width of said upper edge is equal to the width of said lower edge, and each of said side edges has an upper side edge portion that descends in a manner that narrows inward from said upper edge towards said lower edge and a lower side edge portion that extends from that upper edge portion to said lower edge.

5-19. (Canceled)